

AMENDMENT TO THE CLAIMS:

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1. (Canceled)

2. (Previously Presented) An EL display device having a plurality of display pixels comprising an EL element having an emissive layer between first and second electrodes; a first thin film transistor having a first conductive region formed of a semiconductor film and connected to a data line, a gate electrode connected to a gate line, and a second conductive region; and a second thin film transistor having a third conductive region formed of a semiconductor film and connected to a power source line of said EL element, a second gate electrode connected to said second conductive region of said first thin film transistor, and a fourth conductive region connected to said EL element, wherein

an interface between a channel and said fourth conductive region of said second thin film transistor is spaced apart from said emissive layer.

3. (Currently Amended) An EL display device having a plurality of display pixels comprising an EL element having an emissive layer between first and second electrodes, and a thin film transistor having first and second conductive regions formed of a semiconductor film, one of said first and second conductive regions being connected to said EL element, wherein

a light shielding film for shielding light emitted from said EL element is provided between said EL element and an interface between said one of conductive regions connected to said EL element and a channel of said thin film transistor, said light shielding film is conductive.

4. (Original) The EL display device according to claim 3, wherein the first or second electrode of said thin film transistor also functions as said light shielding film.

5. (Original) The EL display device according to claim 3, wherein said light shielding film is provided between said thin film transistor and said EL element disposed on said thin film transistor with an insulating film therebetween, and a second light shielding film is further provided between a transparent substrate on which said thin film transistor is formed and said thin film transistor.

6. (Original) The EL display device according to claim 5, wherein

said second light shielding film has an opening only at a region located inner than an outer edge of an emissive region of said EL element.

7. (Original) The EL display device according to claim 6, wherein
said second light shielding film is connected to a power source for supplying power to
said EL element.

8. (Previously Presented) An EL display device having a plurality of display pixels
comprising:

an EL element having an emissive layer between first and second electrodes;
a first thin film transistor having a first conductive region formed of a
semiconductor film and connected to a data line, a gate electrode connected to a gate line,
and a second conductive region; and

a second thin film transistor having a third conductive region formed of a
semiconductor film and connected to a power source line of said EL element, a second
gate electrode connected to said second conductive region of said first thin film transistor,
and a fourth conductive region connected to said EL element; wherein

a light shielding film for shielding light emitted from said EL element is provided
between said EL element and an interface between a channel and said fourth conductive
region of said second thin film transistor.

9. (Original) The EL display device according to claim 8, wherein a light shielding
film is further provided over the semiconductor film forming an active layer of said first thin
film transistor.

10. (Original) The EL display device according to claim 8, wherein
the first or second electrode of said second thin film transistor also functions as said
light shielding film.

11. (Original) The EL display device according to claim 8, wherein
said light shielding film is electrically connected to said power source line or to a
power source.

12. (Previously Presented) An EL display device having a plurality of display pixels
comprising:

an EL element having an emissive layer between first and second electrodes;

a first thin film transistor having a first conductive region formed of a semiconductor film and connected to a data line, a gate electrode connected to a gate line, and a second conductive region; and

a second thin film transistor having a third conductive region formed of a semiconductor film and connected to a power source line of said EL element, a second gate electrode connected to said second conductive region of said first thin film transistor, and a fourth conductive region connected to said EL element; wherein

a light shielding film for shielding light emitted from said EL element is provided over the semiconductor film forming an active layer of said first thin film transistor and located between said active layer and said EL element.

13. (Original) The EL display device according to claim 12, wherein
the first or second electrode of said first thin film transistor also functions as said light
shielding film.

14. (Original) The EL display device according to claim 12, wherein
said light shielding film is electrically connected to said power source line or to a
power source.

15. (Original) An EL display device having a plurality of display pixels
comprising:

an EL element having an emissive layer between first and second electrodes; and
a thin film transistor having first and second conductive regions formed of a
semiconductor film, one of said first and second conductive regions being connected to
said EL element provided in an upper layer, wherein

a light shielding film having an opening for a portion of said EL element
corresponding to a pixel is provided in a layer underlying said thin film transistor.

16. (Original) The EL display device according to claim 15, wherein a light shielding
film for shielding light emitted from said EL element is further provided in a layer overlying
said thin film transistor.

17. (Original) The EL display device according to claim 15, wherein
said light shielding film is electrically connected to a power source of said EL element.

18. (Original) The EL display device according to claim 15, wherein

the opening of said light shielding film is located inner than an outer edge of an emissive region of said EL element.

19. (Previously Presented) An EL display device having a plurality of display pixels comprising:

an EL element having an emissive layer between first and second electrodes;
a first thin film transistor having a first conductive region formed of a semiconductor film and connected to a data line, a gate electrode connected to a gate line, and a second conductive region; and

a second thin film transistor having a third conductive region formed of a semiconductor film and connected to a power source line of said EL element, a second gate electrode connected to said second conductive region of said first thin film transistor, and a fourth conductive region connected to said EL element provided in an upper layer; wherein

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a light shielding film having an opening corresponding to an emissive region of said EL element is provided in a layer underlying said second thin film transistor.

20. (Original) The EL display device according to claim 19, wherein a light shielding film for shielding light emitted from said EL element is provided in a layer overlying the semiconductor film of at least said second thin film transistor among said first and second thin film transistors.

21. (Original) The EL display device according to claim 19, wherein said light shielding film is electrically connected to a power source of said EL element.

22. (Original) The EL display device according to claim 19, wherein the opening of said light shielding film is located inner than an outer edge of an emissive region of said EL element.

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23. (New) An EL display device having a plurality of display pixels comprising an EL element having an emissive layer between first and second electrodes, and a thin film transistor having first and second conductive regions formed of a semiconductor film, one of said first and second conductive regions being connected to said EL element, wherein a light shielding film for shielding light emitted from said EL element is provided between said EL element and an interface between said one of conductive regions connected to said EL element and a channel of said thin film transistor, said light shielding film is provided between said thin film transistor and said EL element.
